TOSHIBA Field Effect Transistor Silicon N-Channel MOS Type (U-MOS V-H)

# **TPCC8002-H**

High-Efficiency DC-DC Converter Applications Notebook PC Applications Portable Equipment Applications

- Small footprint due to a small and thin package
- High-speed switching
- Small gate charge: Q<sub>SW</sub> = 7.1 nC (typ.)
- Low drain-source ON-resistance:

 $R_{DS (ON)}$  = 7.6 m $\Omega$  (typ.) (  $V_{GS}$  = 4.5 V)

- High forward transfer admittance: |Y<sub>fs</sub>| = 65 S (typ.)
- Low leakage current:  $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 30 \text{ V)}$
- Enhancement mode:  $V_{th}$  = 1.5 to 2.5 V ( $V_{DS}$  = 10 V,  $I_D$  = 1 mA)

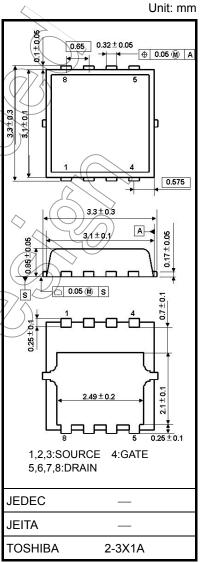
### Absolute Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit	
Drain-source voltage		V <sub>DSS</sub>	30	V	
Drain-gate voltage ( $R_{GS} = 20 \text{ k}\Omega$ )		V <sub>DGR</sub>	30	< <v< td=""></v<>	
Gate-source voltage		V <sub>GS</sub> S	±20	×	
Drain current	DC (Note 1)	<u> </u>	22	A	
	Pulsed (Note 1)	(IDP \	66		
Drain power dissipation (Tc = 25°C)		PD	30	NX	
Drain power dissipation (t = 10 s) (Note 2a)		Po	1.9	w	
Drain power dissipation (t = 10 s) (Note 2b)		PD	0.7	W	
Single-pulse avalanche energy (Note 3)		EAS	126	mJ	
Avalanche current		I <sub>AR</sub>	22	Α	
Repetitive avalanche energy (Tc = 25°C) (Note 4)		EAR	AR 2.1		
Channel temperature		T <sub>ch</sub>	150	°C	
Storage temperature range		T <sub>stg</sub>	–55 to 150	°C	

Note: For Notes 1 to 4, refer to the next page.

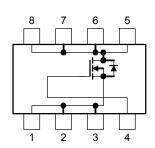
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.



Weight: 0.02 g (typ.)

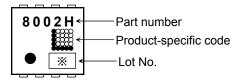
#### **Circuit Configuration**



#### **Thermal Characteristics**

Characteristic	Symbol	Max	Unit
Thermal resistance, channel to case (Tc = 25°C)	R <sub>th (ch-c)</sub>	4.2	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	R <sub>th (ch-a)</sub>	66	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	R <sub>th (ch-a)</sub>	180	°C/W

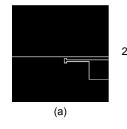
### Marking (Note 5)



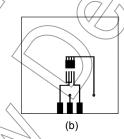
Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a)

(b) Device mounted on a glass-epoxy board (b)



FR-4 25.4 × 25.4 × 0.8 (Unit: mm)



FR-4  $25.4 \times 25.4 \times 0.8$  (Unit: mm)

Note 3:  $V_{DD} = 24 \text{ V}$ ,  $T_{ch} = 25^{\circ}\text{C}$  (initial),  $L = 200 \mu\text{H}$ ,  $R_{G} = 25 \Omega$ ,  $L_{AR} = 22 \text{ A}$ 

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

Note 5: \* Weekly code: (Three digits)

Week of manufacture

(01 for the first week of the year, continuing up to 52 or 53)

Year of manufacture

(The last digit of the year)

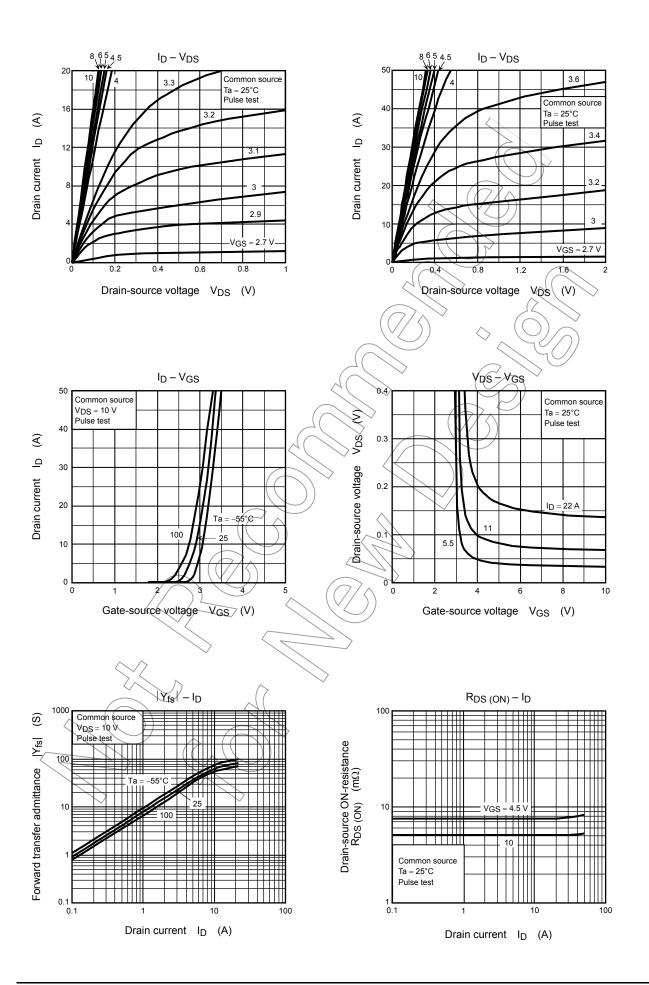
## **Electrical Characteristics (Ta = 25°C)**

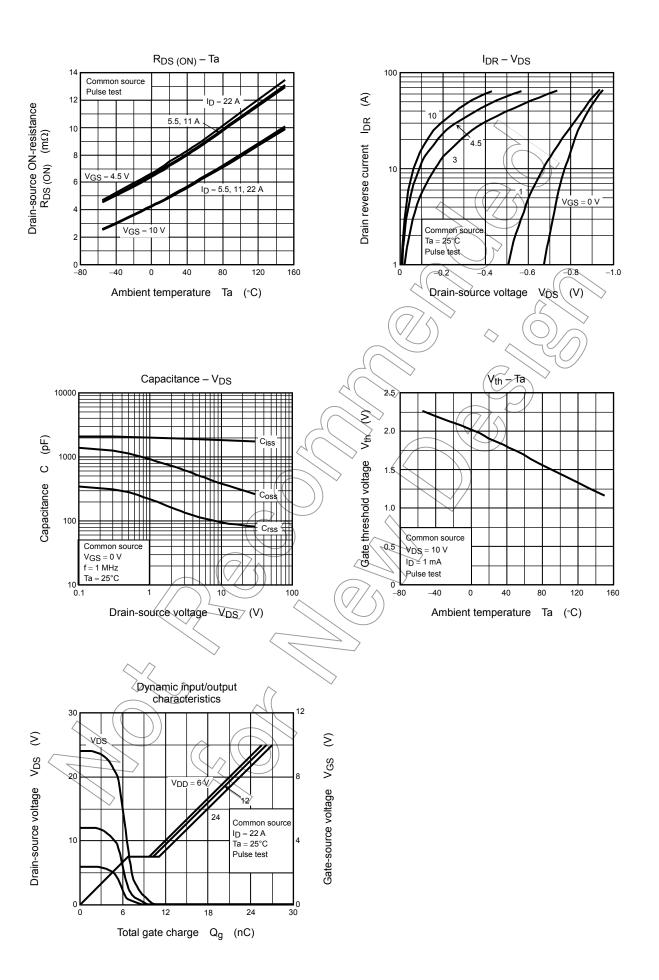
Cha	aracteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage curr	rent	I <sub>GSS</sub>	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±100	nA
Drain cutoff curre	nt	I <sub>DSS</sub>	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V	_	_	10	μА
Drain-source breakdown voltage		V (BR) DSS	$I_D = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	30	_	_	V
		V (BR) DSX	$I_D = 10 \text{ mA}, V_{GS} = -20 \text{ V}$	15		_	v
Gate threshold vo	ltage	$V_{th}$	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$	1.5	) >_	2.5	V
Drain-source ON-resistance		D	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 11 A		7.6	10.6	· mΩ
		R <sub>DS</sub> (ON)	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 11 A	)	5.5	8.3	
Forward transfer a	admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 11 A	33	65	_	S
Input capacitance		C <sub>iss</sub>		_	1900	2500	
Reverse transfer	Reverse transfer capacitance		V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	110	170	pF
Output capacitano	ce	Coss			400	$\rightarrow$	
Gate resistance		rg	V <sub>DS</sub> = 10 V, V <sub>GS</sub> = 0 V, f = 5 MHz	-	3.2	<b>4.8</b>	Ω
Switching time	Rise time	t <sub>r</sub>	V <sub>G</sub> S 0 V I <sub>D</sub> = 11 A C C C C C C C C C C C C C C C C C	7	2.8	) _	ns
	Turn-on time	t <sub>on</sub>		\(\int\)	9.8		
	Fall time	t <sub>f</sub>	4. w w % Z Z Z Z Z Z Z Z Z Z Z Z Z Z Z Z Z		5.9		
	Turn-off time	t <sub>off</sub>	Duty ≤ 1%, t <sub>w</sub> = 10 μs	_	27		
Total gate charge (gate-source plus gate-drain)		Qg	$V_{DD} \approx 24 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 22 \text{ A}$		27		
			$V_{DD} \approx 24 \text{ V}, V_{GS} = 5 \text{ V}, V_{D} \neq 22 \text{ A}$		14.3	_	
Gate-source char	ge 1 (	Q <sub>gs1</sub>			6.8	_	nC
Gate-drain ("Miller") charge		Q <sub>gd</sub>	$V_{DD} \approx 24 \text{ V. V}_{GS} = 10 \text{ V, I}_{D} = 22 \text{ A}$		4.3	_	
Gate switch charg	ge (7/	Q <sub>SW</sub>		_	7.1	_	

# Source-Drain Ratings and Characteristics (Ta = 25°C)

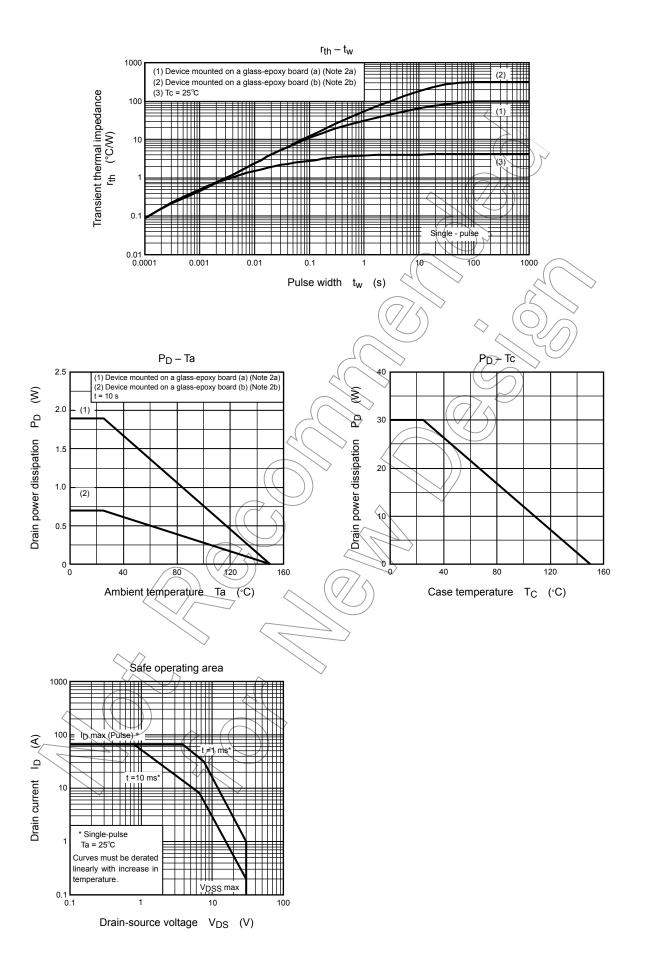
Characteristic	Symbol Test Condition	Min	Тур.	Max	Unit
Drain reverse current Pulse (Note 1)	I <sub>DRP</sub> —		_	66	Α
Forward voltage (diode)	$V_{DSF}$ $I_{DR} = 22 \text{ A}, V_{GS} = 0 \text{ V}$	_	_	-1.2	V

3 2009-07-15





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